Abstracts

26 GHz Coplanar SiGe MMICS (1996 [MCS])

C. Rheinfelder, K. Strohm, F. Beisswanger, J. Gerdes, F.J. Schmuckle, J.-F. Luy and W. Heinrich. "26 GHz Coplanar SiGe MMICS (1996 [MCS])." 1996 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 98. (1996 [MCS]): 205-208.

First results on coplanar MMICs with SiGe HBTs are presented. The circuits are fabricated on high-resistivity Si substrates using a double-mesa HBT process. In the Ka-band, an oscillator output power of 1 dBm and 4.4 dB gain for a one-stage amplifier are achieved. This demonstrates the potential of SiGe transistors for applications in the higher microwave range.

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